

Pages 1-2, paragraph 2 should read

As techniques for removing resist films, presently known are ashing methods in which a resist film to be removed is ashed with oxygen plasma, and heating and dissolving methods in which a resist film to be removed is dissolved using an organic solvent, such as a phenol- or halogen-base organic solvent, with being heated at 90 to 130 °C, or using concentrated sulfuric acid and hydrogen peroxide. Any of these techniques requires a certain time, much energy and a specific chemical material for decomposing or dissolving the resist film. This was a strain on the photolithographic process. In spite of a great demand for new resist removing techniques to replace the above techniques by ashing or dissolving, developments of peeling techniques are yet few. As a representative of such peeling techniques, a new technique has been developed in which a peeling liquid newly developed and the peeling action of high-frequency supersonic waves are used. As such a peeling liquid, the peeling action of "an IPA-H<sub>2</sub>O<sub>2</sub>-base ingredient + salt such as fluoride" has been appreciated.